Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	2.1	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 2.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	96	123	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV120ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV120ENEA	DX%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	2.1	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	8.3	Α
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	T _{j(init)} = 25 °C; I _D = 0.3 A; DUT in avalanche (unclamped)		-	9	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	513	mW
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Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	1.05	W
		T _{sp} = 25 °C		-	6.4	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		,			
I _S	source current	T _{amb} = 25 °C	[1]	-	0.8	Α
ESD maximu	um rating		,		'	_
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

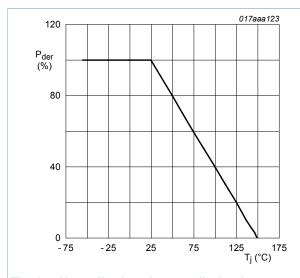


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

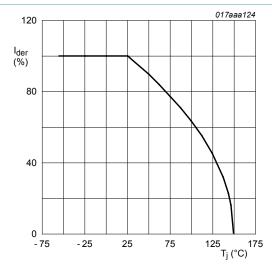


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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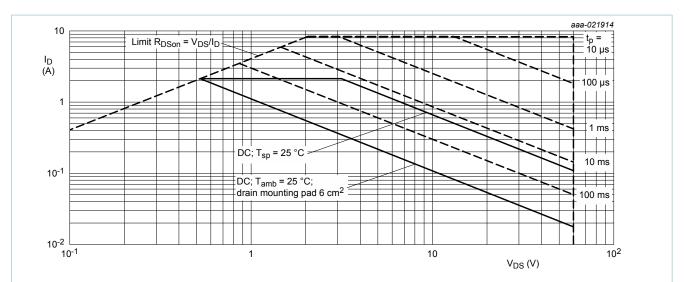


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistan from junction to ambient	thermal resistance		[1]	-	212	244	K/W
			[2]	-	104	119	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

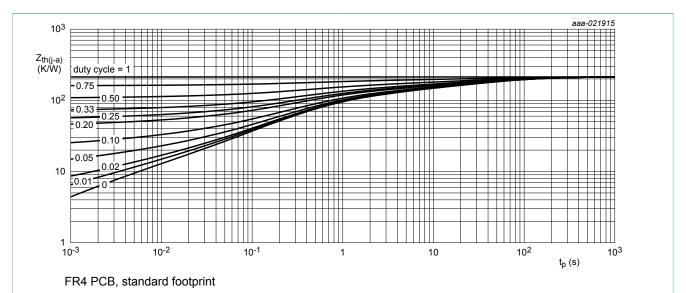


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

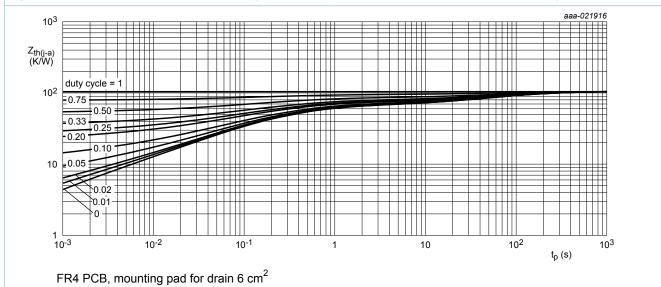


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
acteristics					
drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	1.3	1.7	2.7	V
drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
drain-source on-state	V _{GS} = 10 V; I _D = 2.1 A; T _j = 25 °C	-	96	123	mΩ
resistance	V _{GS} = 10 V; I _D = 2.1 A; T _j = 150 °C	-	192	246	mΩ
	V _{GS} = 4.5 V; I _D = 1.9 A; T _j = 25 °C	-	108	146	mΩ
forward transconductance	V_{DS} = 10 V; I_D = 0.9 A; T_j = 25 °C	-	10.2	-	S
gate resistance	f = 1 MHz	-	10	-	Ω
haracteristics					
total gate charge	$V_{DS} = 30 \text{ V}; I_D = 2.1 \text{ A}; V_{GS} = 10 \text{ V};$	-	5.9	7.4	nC
gate-source charge	T _j = 25 °C	-	0.6	-	nC
gate-drain charge		-	1.1	-	nC
input capacitance	$V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	275	-	pF
output capacitance	T _j = 25 °C	-	24	-	pF
reverse transfer capacitance		-	17	-	pF
turn-on delay time	V_{DS} = 30 V; I_{D} = 2.1 A; V_{GS} = 10 V;	-	6.4	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8.9	-	ns
turn-off delay time		-	15.9	-	ns
fall time		-	6.3	-	ns
in diode	1	1	1	1	
source-drain voltage	I _S = 0.8 A; V _{GS} = 0 V; T _i = 25 °C	_	0.8	1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance haracteristics total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time lin diode	drain-source breakdown voltage gate-source threshold voltage drain leakage current $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 0 \text{ V}; V_{J} = 25 \text{ °C}$ $V_{DS} = 60 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 60 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = 10 \text{ V}; V_{DS} $	acteristics drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 60 gate-source threshold voltage $I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ 1.3 drain leakage current $V_{DS} = 60 \ V; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - gate leakage current $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - drain-source on-state resistance $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - forward transconductance $V_{DS} = 10 \ V; \ I_D = 0.9 \ A; \ T_j = 25 \ ^{\circ}C$ - - forward transconductance $V_{DS} = 30 \ V; \ I_D = 2.1 \ A; \ V_{GS} = 10 \ V;$ - - gate resistance $V_{DS} = 30 \ V; \ I_D = 2.1 \ A; \ V_{GS} = 0 \ V;$ - - total gate charge $V_{DS} = 30 \ V; \ I_D = 2.1$	acteristics drain-source breakdown voltage I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C 60 - gate-source threshold voltage I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C 1.3 1.7 drain leakage current gate leakage current V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C - - gate leakage current gate leakage current V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C - - V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C - - - drain-source on-state resistance V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C - - drain-source on-state resistance V _{GS} = 10 V; I _D = 2.1 A; T _j = 150 °C - - drain-source on-state resistance V _{GS} = 10 V; I _D = 0.9 A; T _j = 25 °C - - - drain-source on-state resistance V _{DS} = 10 V; I _D = 0.9 A; T _j = 25 °C - - - 96 V _{GS} = 10 V; I _D = 2.1 A; V _{GS} = 0 V; T _j = 25 °C - - - 10.2 total gate charge gate resistance f = 1 MHz - 10 - 5.9 gate-source charge gate-drain charge charge gate-drain charge respectance T _j = 25 °C <t< td=""><td>acteristics drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 60 - - gate-source threshold voltage $I_D = 250 \ \mu A; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 1.3 1.7 2.7 drain leakage current voltage $V_{OS} = 60 \ V; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - 1 gate leakage current Vos = 20 \ V; \ V_{OS} = 0 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - 10 Vos = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - - 10 Vos = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - - - drain-source on-state resistance Vos = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C -</td></t<>	acteristics drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 60 - - gate-source threshold voltage $I_D = 250 \ \mu A; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 1.3 1.7 2.7 drain leakage current voltage $V_{OS} = 60 \ V; \ V_{OS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - 1 gate leakage current Vos = 20 \ V; \ V_{OS} = 0 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - 10 Vos = -20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - - 10 Vos = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C - - - - drain-source on-state resistance Vos = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C -

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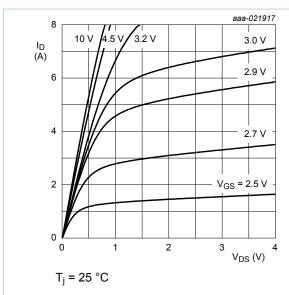


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

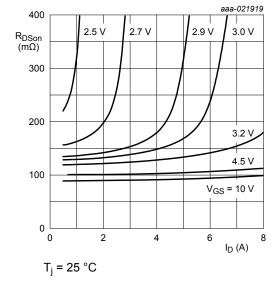


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

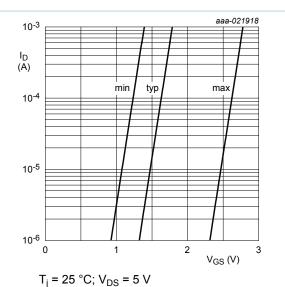


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

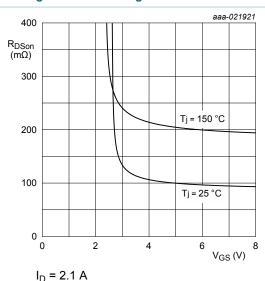


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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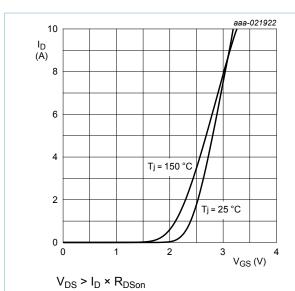


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

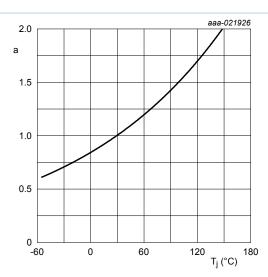


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

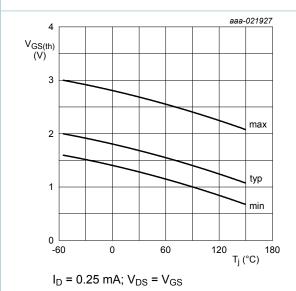


Fig. 12. Gate-source threshold voltage as a function of junction temperature

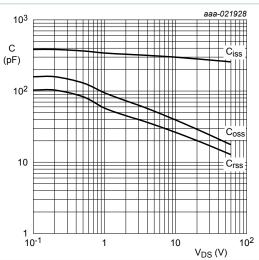


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$

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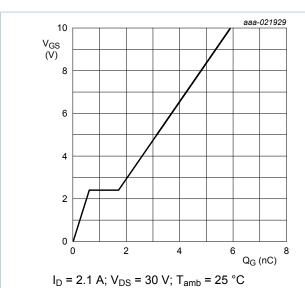


Fig. 14. Gate-source voltage as a function of gate charge; typical values

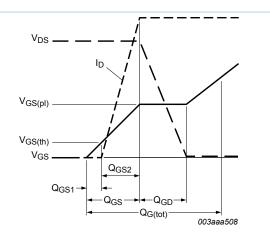


Fig. 15. MOSFET transistor: Gate charge waveform definitions

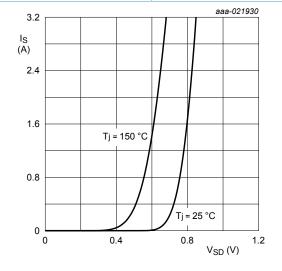
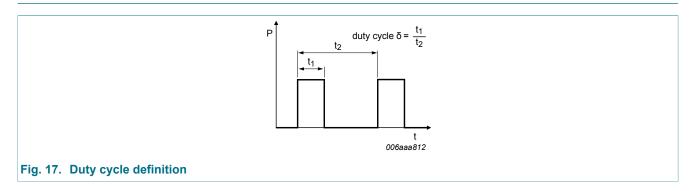


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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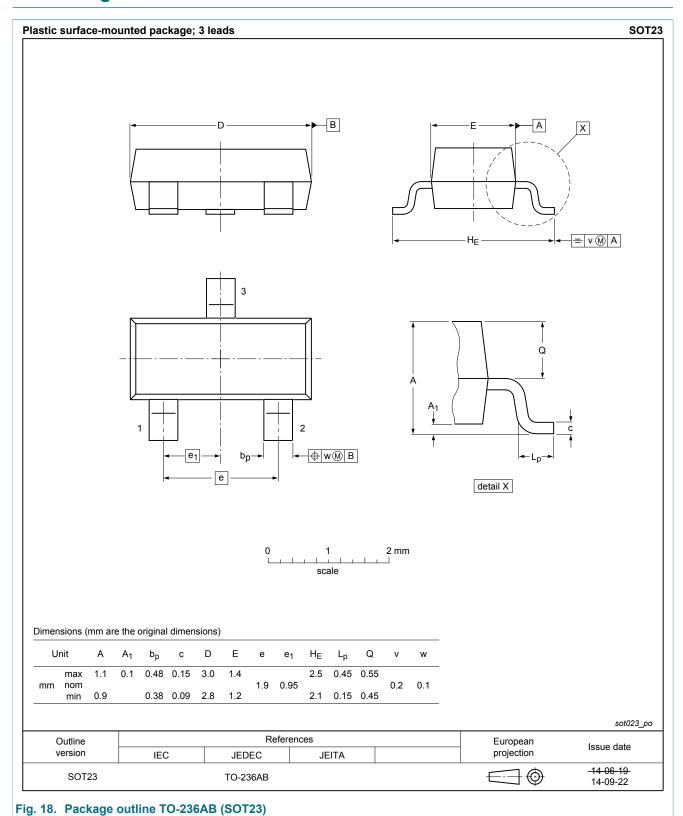
11. Test information



11.1 Quality information

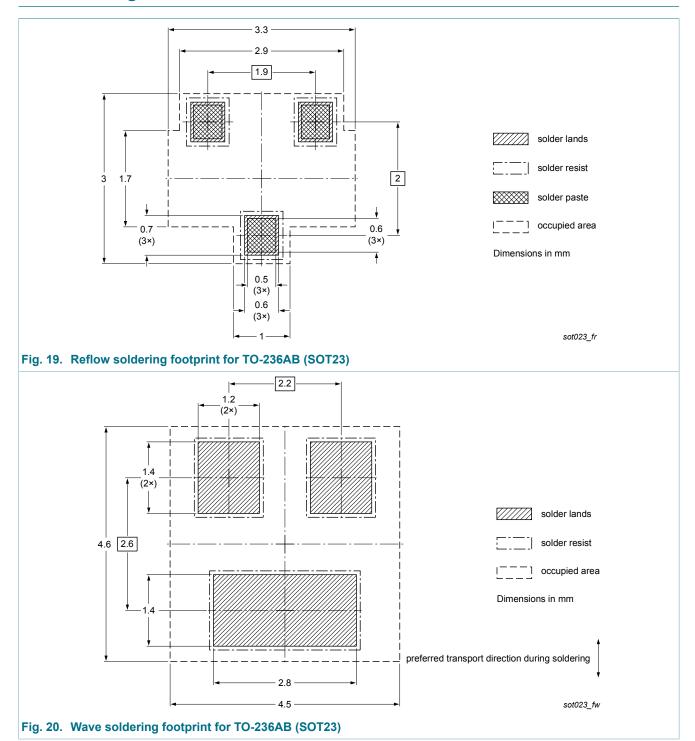
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV120ENEA v.1	20160304	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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